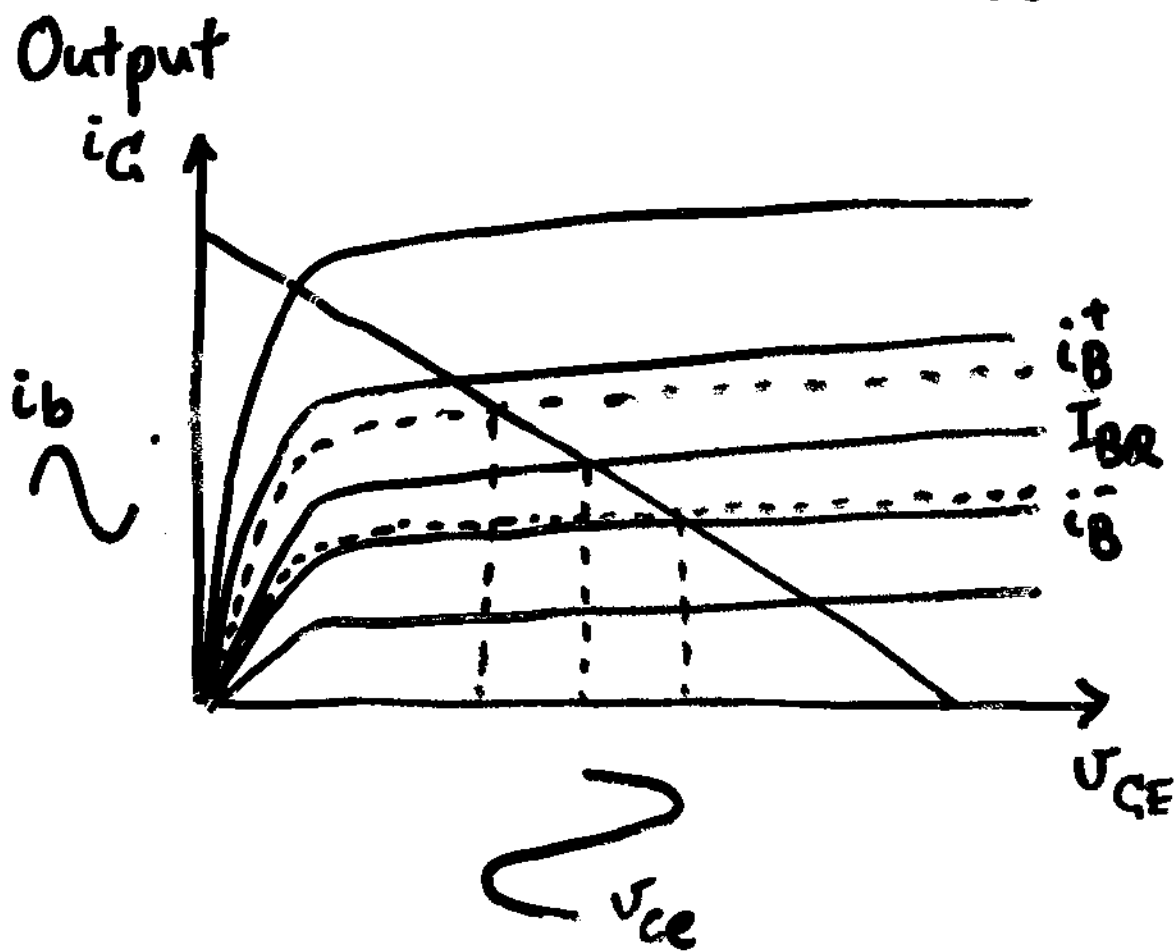
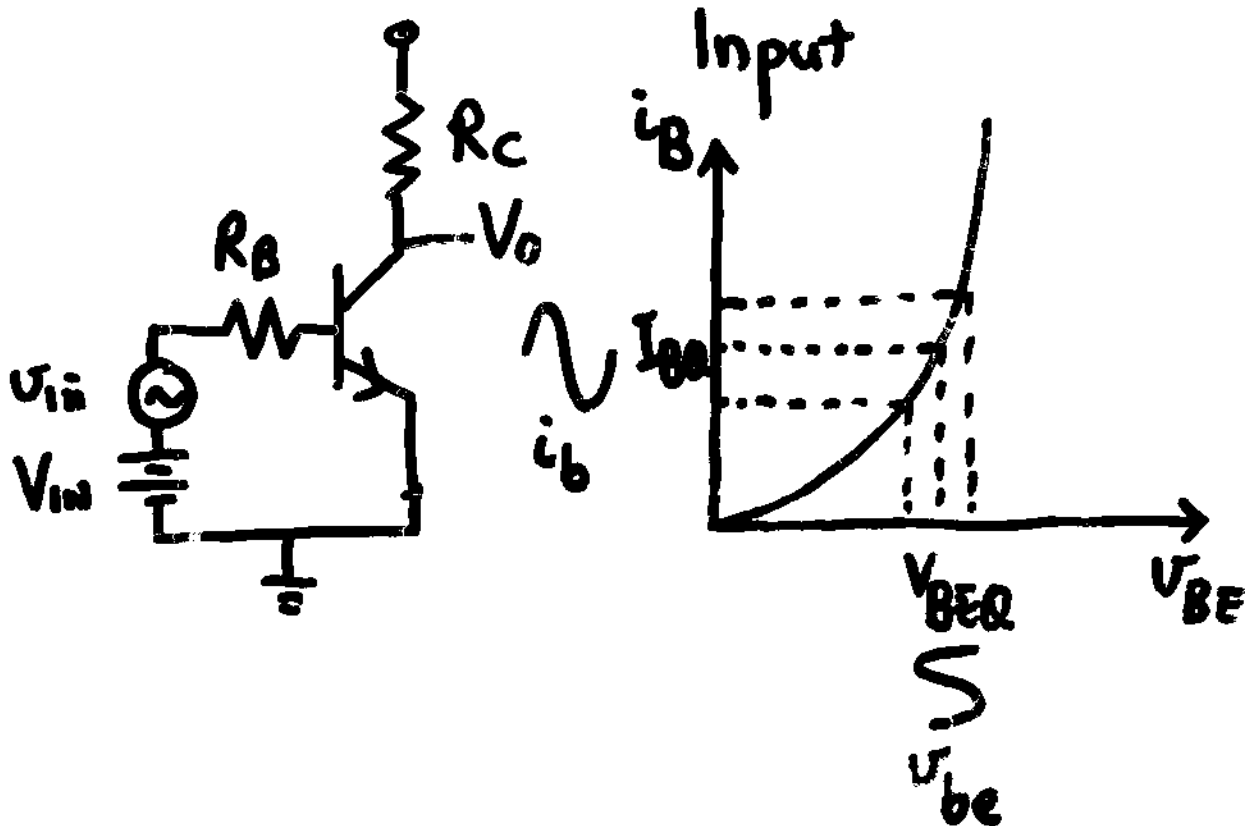


Small-signal model for BJT



$$i_E = I_s e^{V_{BE}/V_T}$$

$$\approx I_s e^{V_{BEQ}/V_T} + I_s e^{V_{BEQ}/V_T} \left(\frac{1}{V_T} v_{be} \right)$$

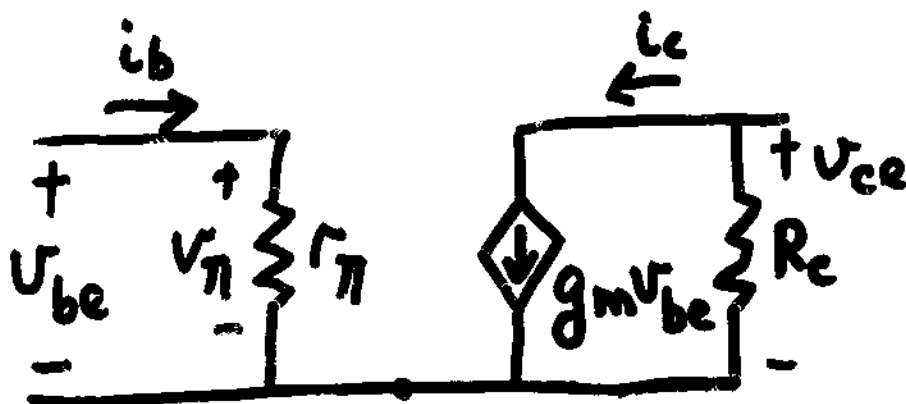
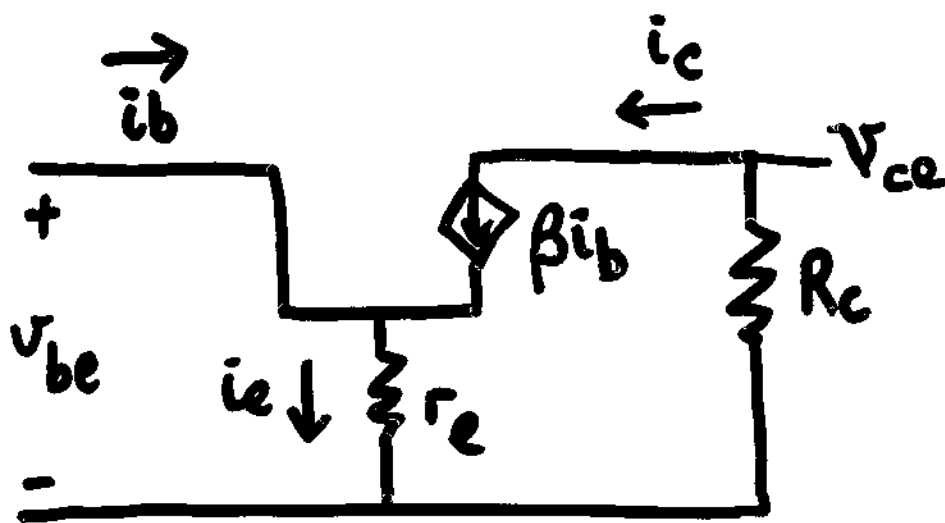
$$\downarrow$$

$$I_{EQ}$$

$$\downarrow$$

$$i_e = v_{be} \frac{I_E}{V_T}$$

$$\Rightarrow r_e = \frac{V_T}{I_E}$$



$$r_\pi = (\beta + 1)r_e$$

$$g_m = \frac{\beta}{r_\pi}$$

Another derivation

$$i_c = \alpha I_s e^{v_{BE}/V_T}$$

$$\approx \alpha I_s e^{v_{BEQ}/V_T} + \alpha I_s e^{v_{BEQ}/V_T} \frac{v_{be}}{V_T}$$

$$\downarrow$$
$$I_{CQ}$$

$$\downarrow$$
$$i_c = v_{be} \frac{I_C}{V_T}$$

$$= g_m v_{be}$$

Transconductance

$$g_m = \frac{I_C}{V_T}$$

$$= \frac{\beta}{r_{\pi}} ?$$

$$r_{\pi} = \frac{v_{be}}{i_b} = \frac{v_{be} \beta}{i_c}$$
$$= \frac{\beta}{g_m}$$

$$\frac{\beta}{(\beta+1)r_e}$$

$$= \frac{\alpha}{V_T/I_E} = \frac{I_C}{V_T}$$

Equivalent (ac) circuit



$$v_{be} = \frac{r_{\pi}}{R_B + r_{\pi}} v_{in}$$

$$i_c = \frac{g_m r_{\pi}}{R_B + r_{\pi}} v_{in} = \frac{\beta}{r_{\pi} + R_B} v_{in}$$

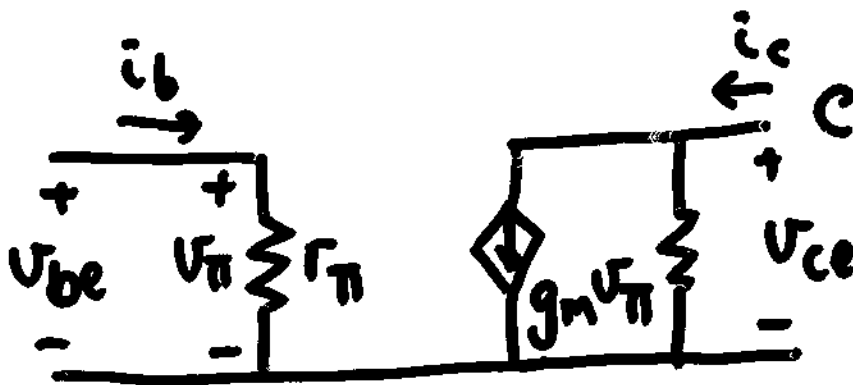
$$v_o = -i_c R_C = -\frac{\beta}{r_{\pi} + R_B} R_C v_{in}$$

$$\begin{aligned} \text{Voltage gain } A_v &= \frac{v_o}{v_{in}} \\ &= \frac{-\beta R_C}{r_{\pi} + R_B} \end{aligned}$$

Early effect

$$I_C = \alpha I_S e^{V_{BE}/V_T} \left[1 + \frac{V_{CE}}{V_A} \right]$$

$$\left. \frac{dI_C}{dV_{CE}} \right|_{V_{CEQ}} = \frac{I_{CQ}}{V_A} \Rightarrow r_o = \frac{V_A}{I_C}$$



Voltage gain $A_v = -g_m r_o r_\pi$

With R_B & R_C ?

$$\begin{aligned} A_v &= -g_m (r_o \parallel R_C) \frac{r_\pi}{r_\pi + R_B} \\ &= -\frac{\beta (r_o \parallel R_C)}{r_\pi + R_B} \end{aligned}$$

Early effect

$$i_C = \left[\alpha I_S e^{V_{BE}/V_T} \right] \left[1 + \frac{V_{CE}}{V_A} \right]$$

$$= \left[\alpha I_S e^{V_{BEQ}/V_T} \cdot e^{V_{be}/V_T} \right] \left[1 + \frac{V_{CEQ}}{V_A} + \frac{V_{ce}}{V_A} \right]$$

$$= \alpha I_S e^{V_{BEQ}/V_T} \cdot \left[1 + \frac{V_{be}}{V_T} \right] \cdot$$

$$\left[1 + \frac{V_{CEQ}}{V_A} + \frac{V_{ce}}{V_A} \right]$$

$$= \alpha I_S e^{V_{BEQ}/V_T} \left[1 + \frac{V_{CEQ}}{V_A} \right]$$

$$+ \alpha I_S e^{V_{BEQ}/V_T} \left[1 + \frac{V_{CEQ}}{V_A} \right] \cdot \frac{V_{be}}{V_A}$$

$$+ \alpha I_S e^{V_{BEQ}/V_T} \frac{V_{ce}}{V_A}$$

$$+ \alpha I_S e^{V_{BEQ}/V_T} \frac{V_{be}}{V_T} \frac{V_{ce}}{V_A}$$

Other effects

1. Series resistance (r_b) of semi-conductor material in base ($\approx 10\Omega$)
2. Reverse-biased diffusion resistance (r_μ) of B-C junction ($\approx M\Omega$)

Typically ignored except for high frequencies

